

Features

Gain: 23dB

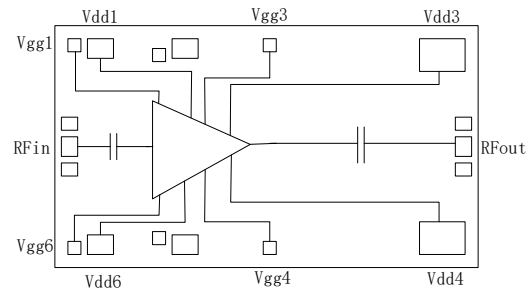
Output P1dB: 33dBm

OIP3: 40dBm

Supply Current: 1150mA@+8V

Chip Size: 4760×2830μm

Functional Diagram

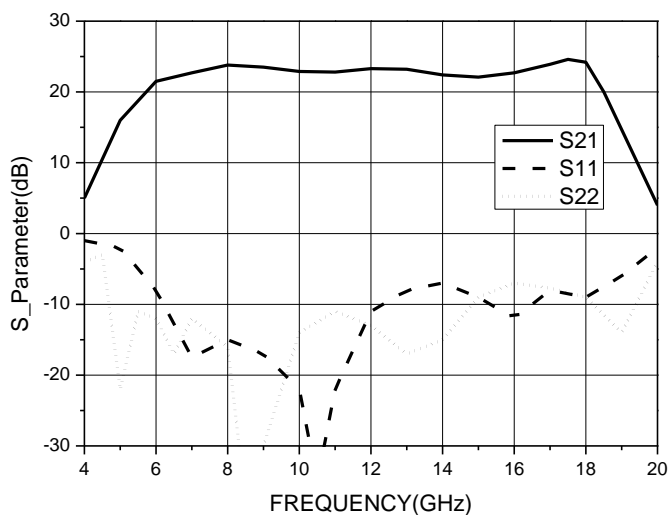


Electrical Specifications, TA = +25°C, Vdd = +8.0V

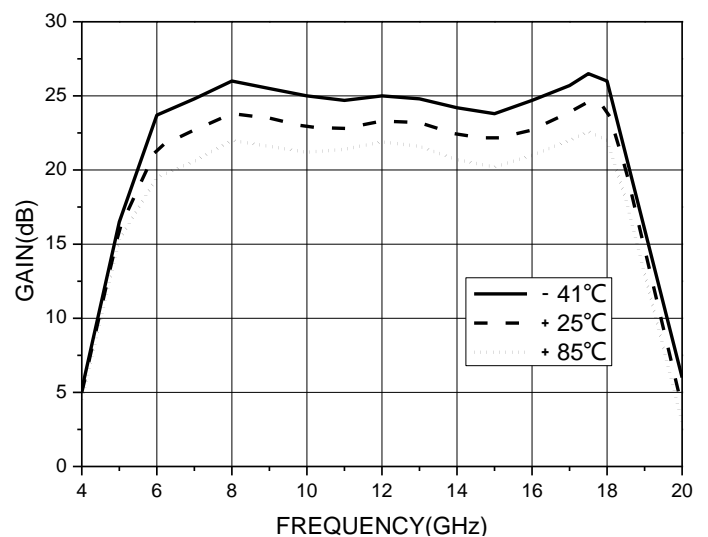
Parameter	Min	Typ	Max	Units
Bandwidth	6		18	GHz
Gain		23		dB
Gain Flatness		±1.5		dB
Input Return Loss		14		dB
Output Return Loss		17		dB
Output Power for 1dB Compression		33		dBm
Output 3 rd Intercept Point		40		dBm
Saturation Output Power		35		dBm
Power Added Efficiency		26		%
Supply Current (@Vdd=8V)		1150		mA

Test Results

S_Parameter

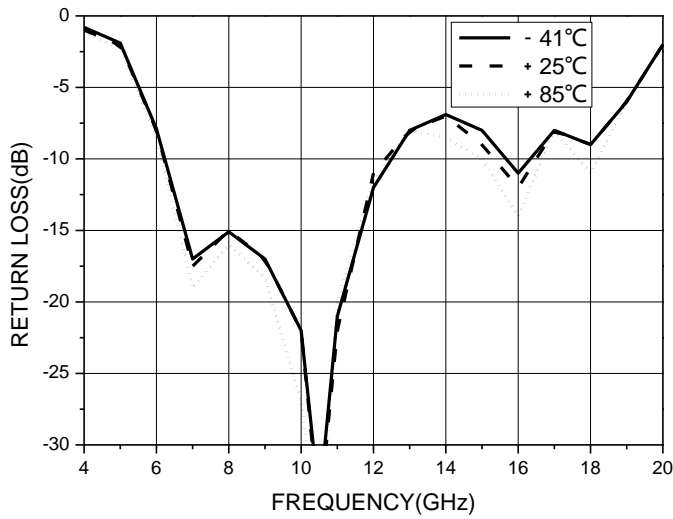


Gain

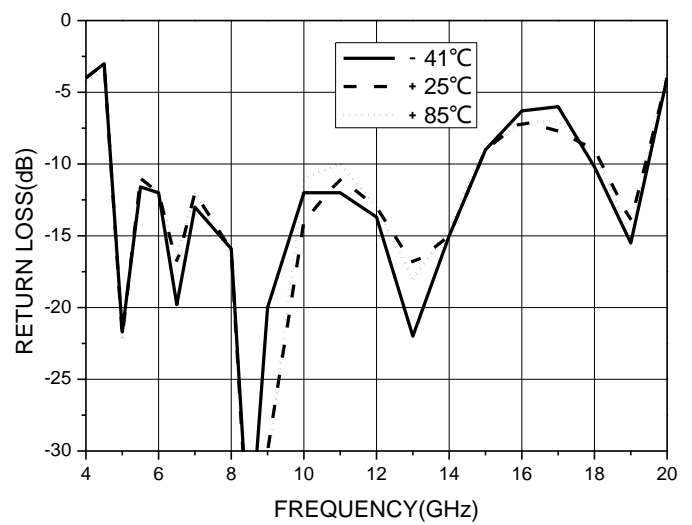




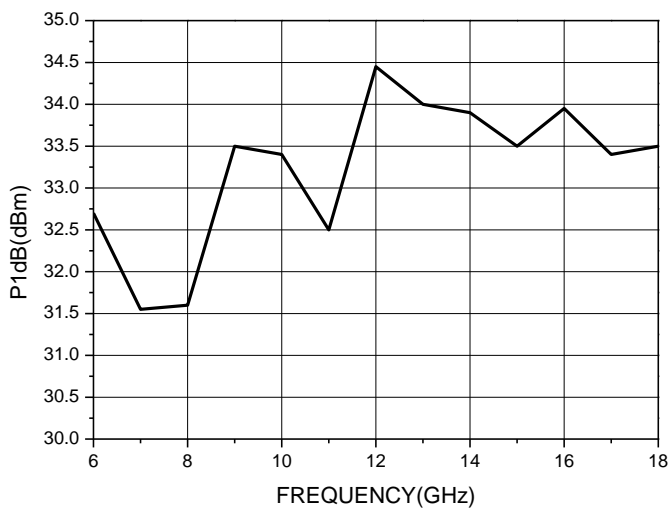
Input Return Loss



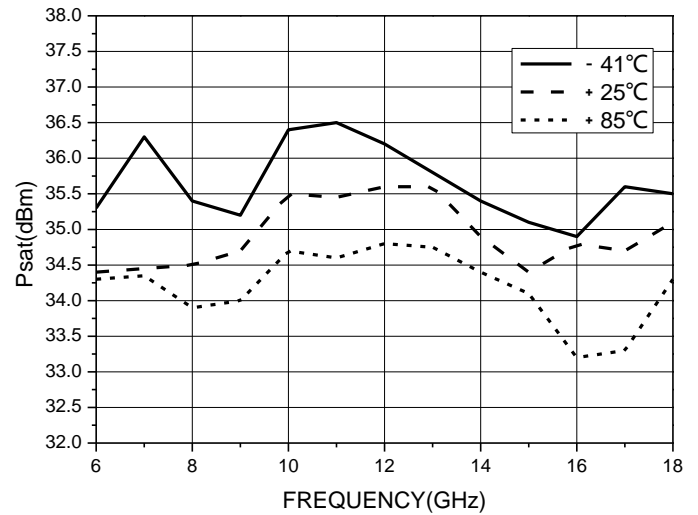
Output Return Loss



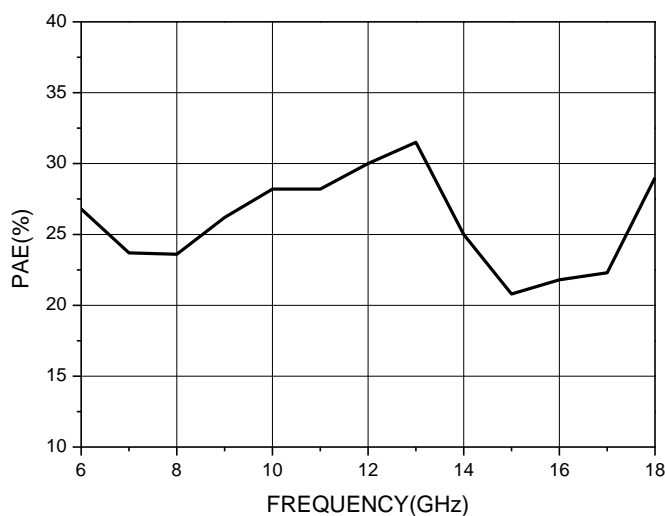
Output P1dB



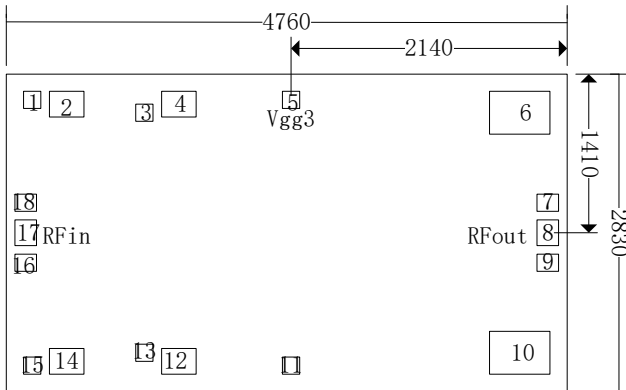
Psat



PAE at Psat



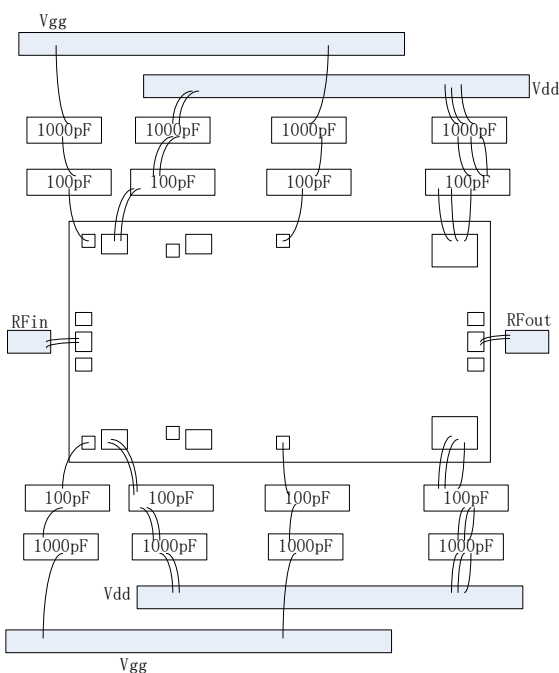
Dimensions (Units: μm)



Pin Description

Pin Number	Features	Description
7、9、16、18	GND	Connect to RF/DC ground
17	RF/IN	RF input, external 50Ohm system
8	RF/OUT	RF output, external 50Ohm system
2、4、6、10、12、14	Vdd	Power supply of Amplifier, external 100pF capacitor
1、3、5、11、13、15	Vgg	The gate of the amplifier controls the power supply. Applying different gate voltages can change the current.

Assembly Diagram



Absolute Maximum Ratings

Collector Bias Voltage	+ 9V
RF Input Power	+ 16dBm
Storage Temperature	-65 - +150°C
Operating Temperature	-55 - +85°C